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(54) **DECOUPLING MIM CAPACITOR**

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(71) Applicant: **INTERNATIONAL BUSINESS
MACHINES CORPORATION,**
ARMONK, NY (US)

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(72) Inventors: **Tao Li**, Slingerlands, NY (US);
Tsung-Sheng Kang, Ballston Lake, NY
(US); **Kangguo Cheng**, Schenectady,
NY (US); **Ruilong Xie**, Niskayuna, NY
(US)

(57)

ABSTRACT

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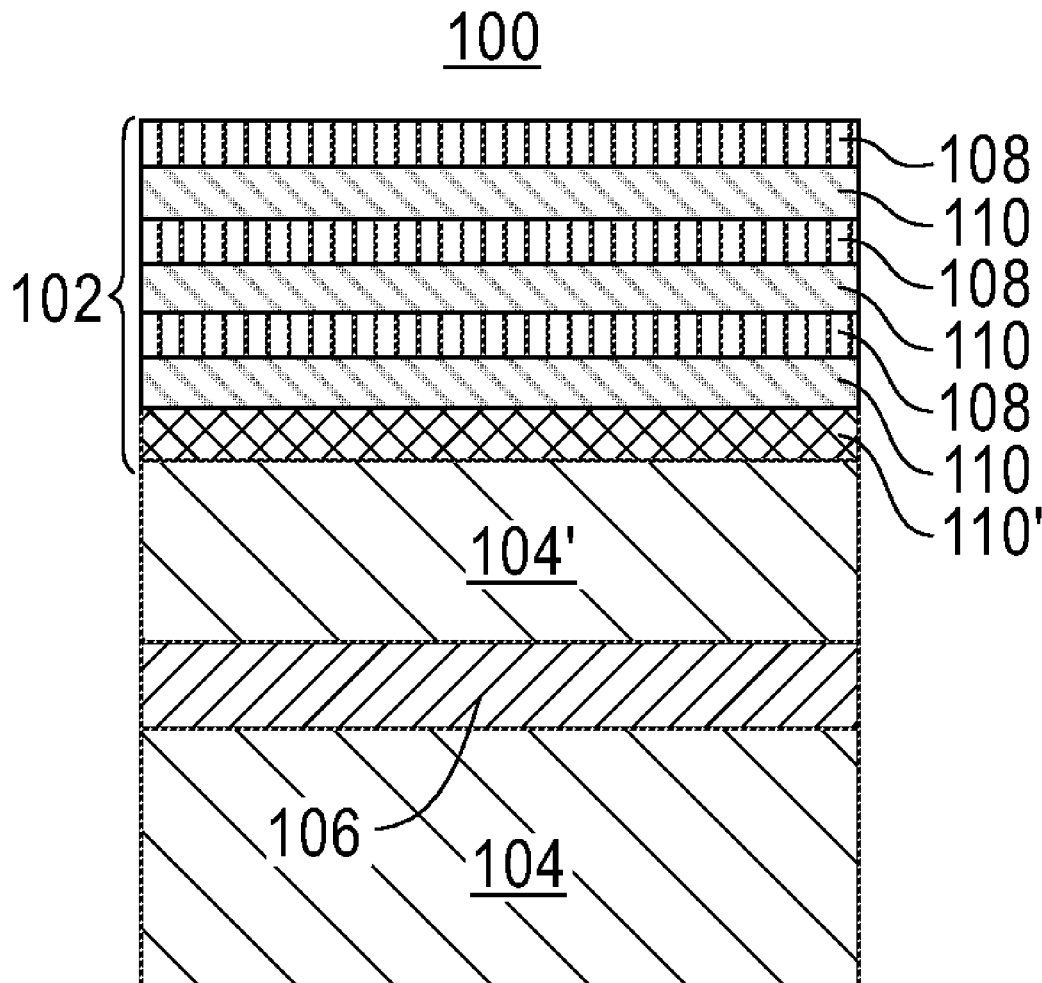
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Semiconductor structures, devices and methods of fabricat-
ing the same, including a semiconductor device that includes
a backside power rail (BSPR), a source-drain (S/D) region
connected to the BSPR, and a metal-insulator-metal capaci-
tor (MIMC), where the BSPR directly connects to the
MIMC by a MIMC via for backside power rail (VBPR)
metal contact.



Section X1